

Amendments to the Claims

Claims 1-33 (Cancelled).

34. (Currently amended) A bit line contact comprising:

~~a layer formed on a substrate and including an opening extending through the layer to a node on the substrate;~~

a first dielectric sidewall spacer formed in the an opening and coating an interior sidewall of the opening, the opening extending to a node on a substrate;

a second dielectric sidewall spacer formed in the opening and coating an interior sidewall of the first dielectric ~~layer~~ sidewall spacer; and

a conductive plug formed within an interior sidewall of the second dielectric ~~layer~~ sidewall spacer and extending through the opening to the node.

35. (Currently amended) The bit line contact of claim 34, wherein the first dielectric sidewall spacer is formed of a first material and the second dielectric sidewall spacer is formed of a second material having a lower relative dielectric constant than the first dielectric sidewall spacer.

36. (Original) The bit line contact of claim 34, wherein the conductive plug comprises doped polysilicon.

37. (Original) The bit line contact of claim 34, wherein the contact is laterally surrounded by six capacitors.

38. (Currently amended) The bit line contact of claim 34, wherein the first dielectric sidewall spacer has an aspect ratio of twenty five or more.

39. (Currently amended) The bit line contact of claim 34, wherein the first dielectric sidewall spacer comprises silicon nitride.

40. (Currently amended) The bit line contact of claim 34, wherein the second dielectric sidewall spacer comprises silicon dioxide.

41. (Currently amended) The bit line contact of claim 34, wherein the second dielectric sidewall spacer is thicker than the first dielectric sidewall spacer.